

## CMOS Static RAM 1 Meg (128K x 8-Bit) Revolutionary Pinout

### **Features**

- 128K x 8 advanced high-speed CMOS static RAM
- JEDEC revolutionary pinout (center power/GND) for reduced noise.
- Equal access and cycle times
  - Commercial: 12/15/20ns
  - Industrial: 15/20ns
- One Chip Select plus one Output Enable pin
- Bidirectional inputs and outputs directly TTL-compatible
- Low power consumption via chip deselect
- Available in a 32-pin 400 mil Plastic SOJ.

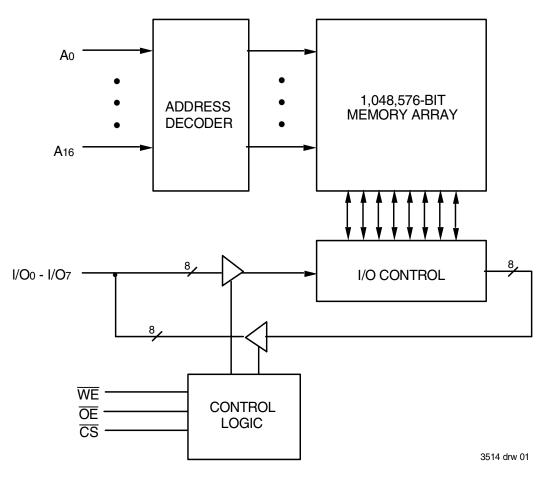
# Description

The IDT71124 is a 1,048,576-bit high-speed static RAM organized as 128K x 8. It is fabricated using high-performance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs. The JEDEC centerpower/GND pinout reduces noise generation and improves system performance.

The IDT71124 has an output enable pin which operates as fast as 6ns, with address access times as fast as 12ns available. All bidirectional inputs and outputs of the IDT71124 are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used; no clocks or refreshes are required for operation.

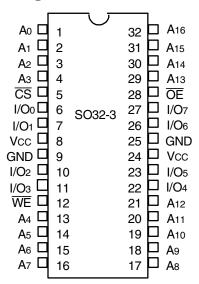
The IDT71124 is packaged in a 32-pin 400 mil Plastic SOJ.





**APRIL 2013** 

### Pin Configuration



3514 drw 02

SOJ **Top View** 

### Truth Table<sup>(1,2)</sup>

CS	ŌĒ	WE	I/O	Function
L	L	Н	DATAOUT	Read Data
L	Х	L	DATAIN	Write Data
L	Н	Н	High-Z	Output Disabled
Н	Х	Х	High-Z	Deselected - Standby (ISB)
VHC <sup>(3)</sup>	Х	Х	High-Z	Deselected - Standby (ISB1)

NOTES:

1.  $H = V_{H}, L = V_{IL}, x = Don't care.$ 2. VLC = 0.2V, VHC = VCC - 0.2V.3. Other inputs  $\ge VHC$  or  $\le VLC.$ 

## Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Value	Unit
Vterm <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0 <sup>(2)</sup>	V
Та	Operating Temperature	0 to +70	٥C
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-55 to +125	٥C
Рт	Power Dissipation	1.25	W
Ιουτ	DC Output Current	50	mA
NOTEC	•	•	3514 tbl 02

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed Vcc + 0.5V.

#### Capacitance $(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter <sup>(1)</sup> Conditions Max		Max.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Ci/o	I/O Capacitance	Vout = 3dV	8	pF
				3514 tbl 03

NOTE:

3514 tbl 01

1. This parameter is guaranteed by device characterization, but is not production tested.

## **Recommended Operating Temperature and Supply Voltage**

Grade	Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V ± 10%
Industrial	-40°C to +85°C	0V	5.0V ± 10%

3514 tbl 04

## **Recommended DC Operating** Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	۷
Viн	Input High Voltage	2.2		Vcc +0.5	۷
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>		0.8	V

3514 tbl 05

## **DC Electrical Characteristics**

#### (Vcc = 5.0V ± 10%, Commercial and Industrial Temperature Ranges)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
LI	Input Leakage Current	Vcc = Max., VIN = GND to Vcc	_	5	μA
Ilo	Output Leakage Current	Vcc = Max., $\overline{\text{CS}}$ = VIH, VOUT = GND to Vcc	_	5	μA
Vol	Output Low Voltage	Iol = 8mA, Vcc = Min.		0.4	V
Vон	Output High Voltage	Iон = -4mA, Vcc = Min.	2.4		V

3514 tbl 06

# DC Electrical Characteristics<sup>(1)</sup>

#### $(Vcc = 5.0V \pm 10\%, VLc = 0.2V, VHc = Vcc - 0.2V)$

		71124S12	71124S15		71124S20		
Symbol	Parameter	Com'l.	Com'l.	Ind.	Com'l.	Ind.	Unit
lcc	Dynamic Operating Current $\overline{CS} \leq VIL$ , Outputs Open, Vcc = Max., f = fmax <sup>(2)</sup>	160	155	155	140	140	mA
lsв	Standby Power Supply Current (TTL Level) $\overline{\text{CS}} \ge \text{Vih}$ , Outputs Open, Vcc = Max., f = fmax <sup>(2)</sup>	40	40	40	40	40	mA
ISB1	$ \begin{array}{l} \mbox{Full Standby Power Supply Current (CMOS Level)} \\ \hline $	10	10	10	10	10	mA
NOTES:	·	-		-	-	3	514 tbl 07

NOTES:

1. All values are maximum guaranteed values.

2. fmax = 1/trc (all address inputs are cycling at fmax); f = 0 means no address input lines are changing.

## **AC Test Conditions**

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figure 1 and 2

3514 tbl 08

# AC Test Loads

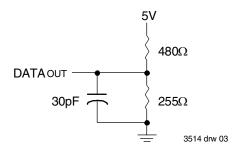
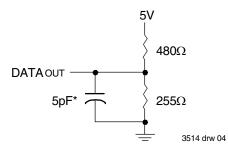


Figure 1. AC Test Load



\*Including jig and scope capacitance.

Figure 2. AC Test Load (for tclz, tolz, tchz, tohz, tow, and twhz)

3514 tbl 09

# **AC Electrical Characteristics**

(Vcc = 5.0V ± 10%, Commercial and Industrial Temperature Ranges)

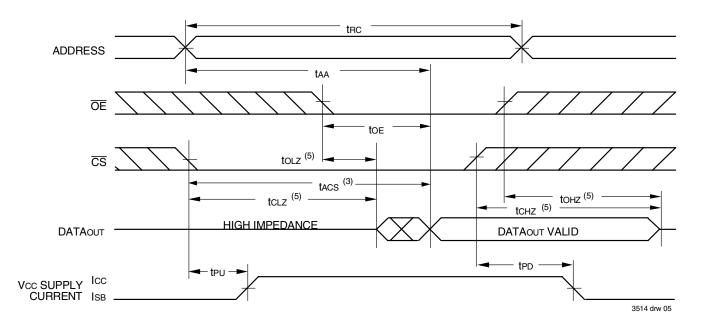
		71124	4S12 <sup>(2)</sup>	71124S15		71124S20		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	12		15		20		ns
taa	Address Access Time		12		15		20	ns
tacs	Chip Select Access Time		12		15		20	ns
tclz <sup>(1)</sup>	Chip Select to Output in Low-Z	3		3	_	3		ns
tснz <sup>(1)</sup>	Chip Deselect to Output in High-Z	0	6	0	7	0	8	ns
toe	Output Enable to Output Valid		6		7		8	ns
tolz <sup>(1)</sup>	Output Enable to Output in Low-Z	0		0		0		ns
tонz <sup>(1)</sup>	Output Disable to Output in High-Z	0	5	0	5	0	7	ns
tон	Output Hold from Address Change	4		4		4		ns
tpu <sup>(1)</sup>	Chip Select to Power-Up Time	0		0		0		ns
tPD <sup>(1)</sup>	Chip Deselect to Power-Down Time		12		15		20	ns
WRITE CYCL	E							
twc	Write Cycle Time	12		15		20		ns
taw	Address Valid to End of Write	8		12		15		ns
tcw	Chip Select to End of Write	8	_	12	_	15		ns
tas	Address Set-up Time	0	_	0	_	0		ns
twp	Write Pulse Width	8		12	_	15		ns
twr	Write Recovery Time	0	_	0	_	0		ns
tow	Data Valid to End-of-Write	6		8		9		ns
tDH	Data Hold Time	0		0		0		ns
tow <sup>(1)</sup>	Output active from End-of-Write	3		3		4	_	ns
twнz <sup>(1)</sup>	Write Enable to Output in High-Z	0	5	0	5	0	8	ns

NOTE:

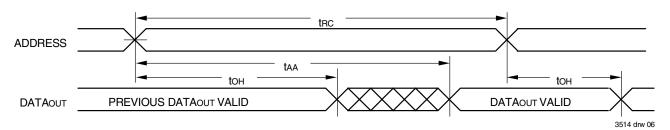
1. This parameter guaranteed with the AC load (Figure 2) by device characterization, but is not production tested.

2. There is no industrial temperature offering for the 12ns speed grade.

# Timing Waveform of Read Cycle No. 1<sup>(1)</sup>



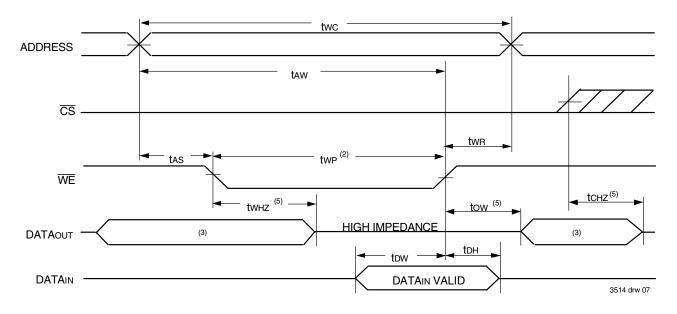
# Timing Waveform of Read Cycle No. 2<sup>(1,2,4)</sup>



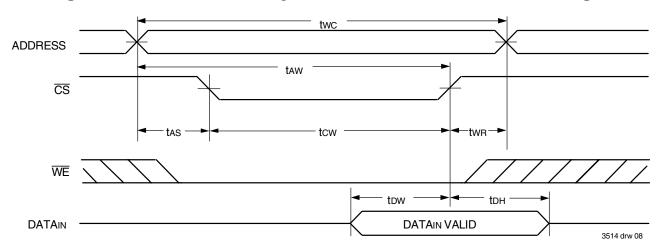
#### NOTES:

- 1. WE is HIGH for Read Cycle.
- 2. Device is continuously selected,  $\overline{CS}$  is LOW.
- 3. Address must be valid prior to or coincident with the later of  $\overline{CS}$  transition LOW; otherwise taa is the limiting parameter.
- 4. OE is LOW.
- 5. Transition is measured ±200mV from steady state.

Timing Waveform of Write Cycle No. 1 (WE Controlled Timing)<sup>(1,2,4)</sup>



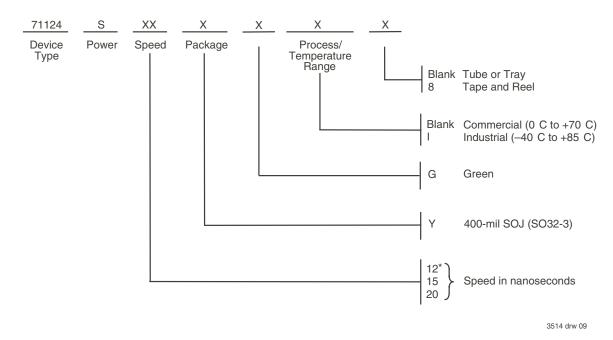
Timing Waveform of Write Cycle No. 2 (CS Controlled Timing)<sup>(1,4)</sup>



#### NOTES:

- 1. A write occurs during the overlap of a LOW  $\overline{CS}$  and a LOW  $\overline{WE}$ .
- 2.  $\overline{OE}$  is continuously HIGH. During a  $\overline{WE}$  controlled write cycle with  $\overline{OE}$  LOW, twp must be greater than or equal to twHz + tow to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If  $\overline{OE}$  is HIGH during a  $\overline{WE}$  controlled write cycle, this requirement does not apply and the minimum write pulse is the specified twp.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4. If the  $\overline{CS}$  LOW transition occurs simultaneously with or after the  $\overline{WE}$  LOW transition, the outputs remain in a high impedance state.  $\overline{CS}$  must be active during the tcw write period.
- 5. Transition is measured  $\pm 200 \text{mV}$  from steady state.

# **Ordering Information**



\* No industrial temp on 12ns speed

## **Datasheet Document History**

08/05/99:		Updated to new format
	Pg. 3	Removed military entries on DC table
	Pg. 4	Removed Note 1 and renumbered footnotes
	Pg. 6	Revised footnotes on Write Cycle No. 1 diagram
08/13/99:	Pg. 8	Added Datasheet Document History
09/30/99:	Pg. 1, 3, 4, 7	Added 12ns, 15ns, and 20ns industrial temperature speed grade offerings
02/18/00:	Pg. 3	Revise IsB for Industrial Temperature offerings to meet commerical specifications
03/14/00:	Pg. 3	Revised IsB to accomidate speed functionality
04/01/00:	Pg.4	Tightened tAW, tCW, tWP and tDW within the AC Electrical Characteristics
08/09/00:		Not recommended for new designs
02/01/01:		Removed "Not recommended for new designs"
10/23/08:	Pg.7	Removed "IDT" from the orderable part number
04/02/13:	Pg.1	Removed 12ns speed from the Industrial temp offering. Removed IDT in reference to fabrication
	Pg.3	Removed the industrial 12ns speed grade information from the DC Electrical Chars table 07
	Pg.4	Added footnote 2 to AC Electrical Chars table 09 to indicate that there is no industrial 12ns speed
	Pg.7	Added Tape & Reel and Green designators to the ordering information. Added a footnote to the
		ordering information to indicate that there is no industrial 12ns speed offering



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